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Kind regards,

Team Nexperia



# PBHV8118T

180 V, 1 A NPN high-voltage low  $V_{CEsat}$  (BISS) transistor

Rev. 01 — 7 May 2010

Product data sheet

## 1. Product profile

### 1.1 General description

NPN high-voltage low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

### 1.2 Features and benefits

- High voltage
- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain ( $h_{FE}$ ) at high  $I_C$
- AEC-Q101 qualified
- Small SMD plastic package

### 1.3 Applications

- LED driver for LED chain module
- LCD backlighting
- Automotive power management
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

### 1.4 Quick reference data

Table 1. Quick reference data

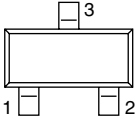
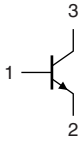
| Symbol    | Parameter                 | Conditions                                      | Min     | Typ | Max | Unit |
|-----------|---------------------------|---|---------|-----|-----|------|
| $V_{CEO}$ | collector-emitter voltage | open base                                       | -       | -   | 180 | V    |
| $I_C$     | collector current         |   | -       | -   | 1   | A    |
| $h_{FE}$  | DC current gain           | $V_{CE} = 10\text{ V};$<br>$I_C = 50\text{ mA}$ | [1] 100 | 250 | -   |      |

[1] Pulse test:  $t_p \leq 300\ \mu\text{s}; \delta \leq 0.02$ .



## 2. Pinning information

Table 2. Pinning

| Pin | Description | Simplified outline  | Graphic symbol  |
|-----|-------------|---|---|
| 1   | base        |  |  |
| 2   | emitter     |   |   |
| 3   | collector   |   |   |

*sym021*

## 3. Ordering information

Table 3. Ordering information

| Type number | Package |  |         |
|-------------|---------|--|---------|
|             | Name    | Description                              | Version |
| PBHV8118T   | -       | plastic surface-mounted package; 3 leads | SOT23   |

## 4. Marking

Table 4. Marking codes

| Type number | Marking code <sup>[1]</sup> |
|-------------|-----------------------------|
| PBHV8118T   | LZ*                         |

- [1] \* = -: made in Hong Kong  
 \* = p: made in Hong Kong  
 \* = t: made in Malaysia  
 \* = W: made in China

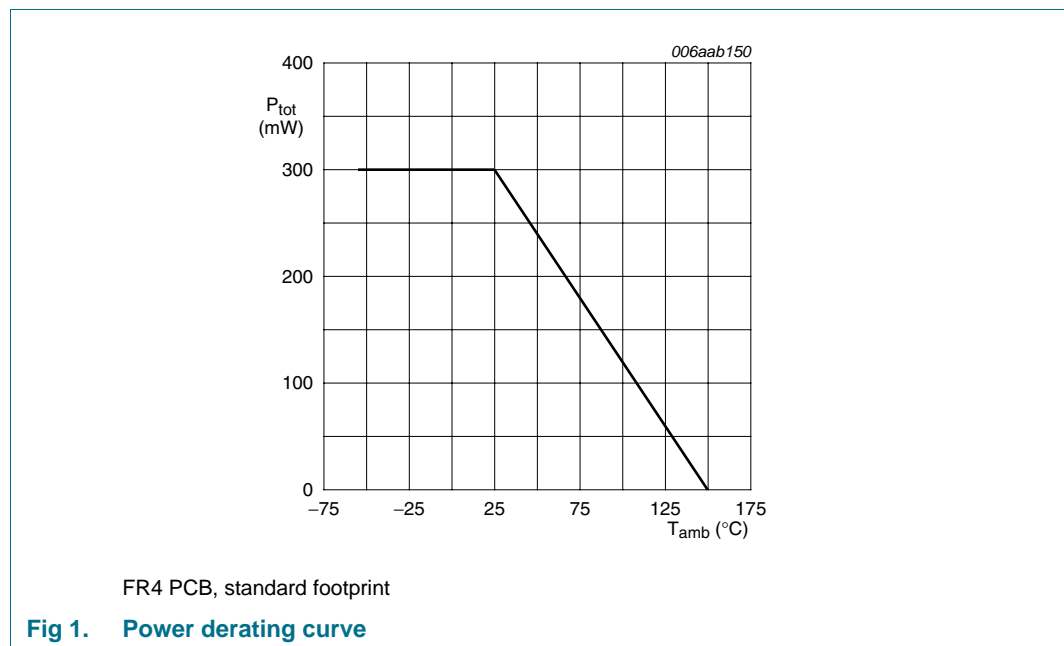
## 5. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol    | Parameter                 | Conditions                       | Min | Max  | Unit |
|-----------|---------------------------|----------------------------------|-----|------|------|
| $V_{CBO}$ | collector-base voltage    | open emitter                     | -   | 400  | V    |
| $V_{CEO}$ | collector-emitter voltage | open base                        | -   | 180  | V    |
| $V_{EBO}$ | emitter-base voltage      | open collector                   | -   | 6    | V    |
| $I_C$     | collector current         |                                  | -   | 1    | A    |
| $I_{CM}$  | peak collector current    | single pulse;<br>$t_p \leq 1$ ms | -   | 2    | A    |
| $I_{BM}$  | peak base current         | single pulse;<br>$t_p \leq 1$ ms | -   | 400  | mA   |
| $P_{tot}$ | total power dissipation   | $T_{amb} \leq 25$ °C             | [1] | 300  | mW   |
| $T_j$     | junction temperature      |                                  | -   | 150  | °C   |
| $T_{amb}$ | ambient temperature       |                                  | -55 | +150 | °C   |
| $T_{stg}$ | storage temperature       |                                  | -65 | +150 | °C   |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

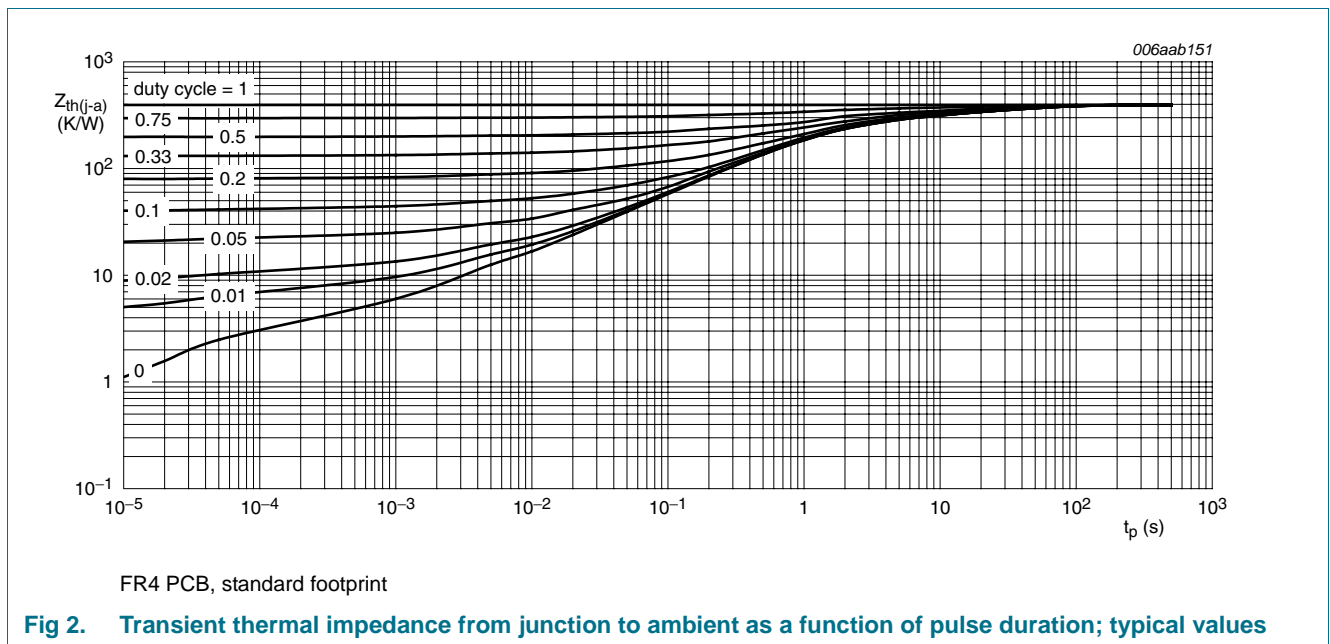


## 6. Thermal characteristics

**Table 6. Thermal characteristics**

| Symbol         | Parameter  | Conditions  | Min | Typ | Max | Unit |
|----------------|--|-------------|-----|-----|-----|------|
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | in free air | [1] | -   | 417 | K/W  |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |             | -   | -   | 70  | K/W  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



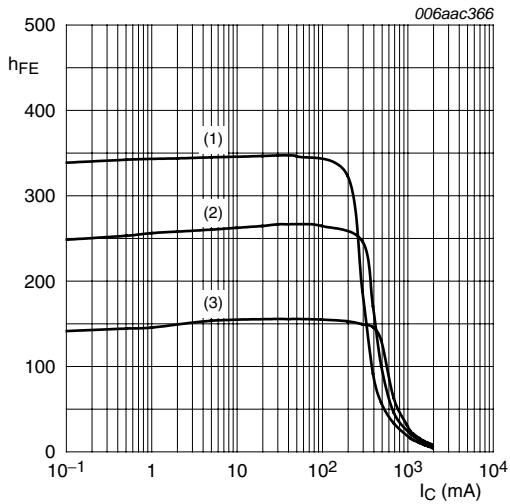
**Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

## 7. Characteristics

**Table 7. Characteristics**
 $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

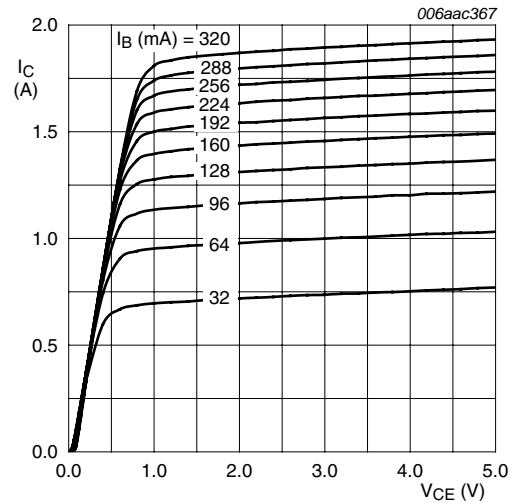
| Symbol      | Parameter                            | Conditions  | Min | Typ  | Max | Unit          |    |
|-------------|--------------------------------------|---|-----|------|-----|---------------|----|
| $I_{CBO}$   | collector-base cut-off current       | $V_{CB} = 144\text{ V}; I_E = 0\text{ A}$   | -   | -    | 100 | nA            |    |
|             |                                      | $V_{CB} = 144\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$                | -   | -    | 10  | $\mu\text{A}$ |    |
| $I_{CES}$   | collector-emitter cut-off current    | $V_{CE} = 144\text{ V}; V_{BE} = 0\text{ V}$  | -   | -    | 100 | nA            |    |
| $I_{EBO}$   | emitter-base cut-off current         | $V_{EB} = 4\text{ V}; I_C = 0\text{ A}$   | -   | -    | 100 | nA            |    |
| $h_{FE}$    | DC current gain                      | $V_{CE} = 10\text{ V}$  | [1] |      |     |               |    |
|             |                                      | $I_C = 50\text{ mA}$  | 100 | 250  | -   |               |    |
|             |                                      | $I_C = 100\text{ mA}$   | 100 | 250  | -   |               |    |
|             |                                      | $I_C = 0.5\text{ A}$  | 50  | 100  | -   |               |    |
| $V_{CEsat}$ | collector-emitter saturation voltage | $I_C = 100\text{ mA}; I_B = 10\text{ mA}$   | [1] | -    | 40  | 60            | mV |
|             |                                      | $I_C = 100\text{ mA}; I_B = 20\text{ mA}$   | [1] | -    | 33  | 50            | mV |
| $V_{BEsat}$ | base-emitter saturation voltage      | $I_C = 0.5\text{ A}; I_B = 100\text{ mA}$   | [1] | -    | 1   | 1.2           | V  |
| $t_d$       | delay time                           | $V_{CC} = 6\text{ V}; I_C = 0.5\text{ A}; I_{Bon} = 0.1\text{ A}; I_{Boff} = -0.1\text{ A}$ | -   | 7    | -   | ns            |    |
| $t_r$       | rise time                            |   | -   | 565  | -   | ns            |    |
| $t_{on}$    | turn-on time                         |   | -   | 572  | -   | ns            |    |
| $t_s$       | storage time                         |   | -   | 1320 | -   | ns            |    |
| $t_f$       | fall time                            |   | -   | 740  | -   | ns            |    |
| $t_{off}$   | turn-off time                        |   | -   | 2060 | -   | ns            |    |
| $f_T$       | transition frequency                 | $V_{CE} = 10\text{ V}; I_C = 10\text{ mA}; f = 100\text{ MHz}$                              | -   | 30   | -   | MHz           |    |
| $C_c$       | collector capacitance                | $V_{CB} = 20\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$                            | -   | 5.7  | -   | pF            |    |
| $C_e$       | emitter capacitance                  | $V_{EB} = 0.5\text{ V}; I_C = i_c = 0\text{ A}; f = 1\text{ MHz}$                           | -   | 150  | -   | pF            |    |

[1] Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .



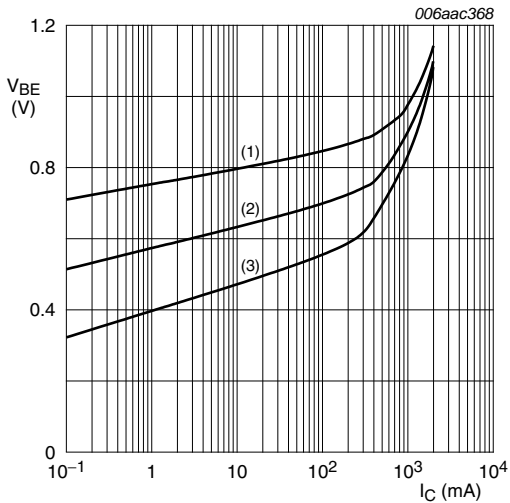
$V_{CE} = 10\text{ V}$   
 (1)  $T_{amb} = 100^\circ C$   
 (2)  $T_{amb} = 25^\circ C$   
 (3)  $T_{amb} = -55^\circ C$

**Fig 3. DC current gain as a function of collector current; typical values**



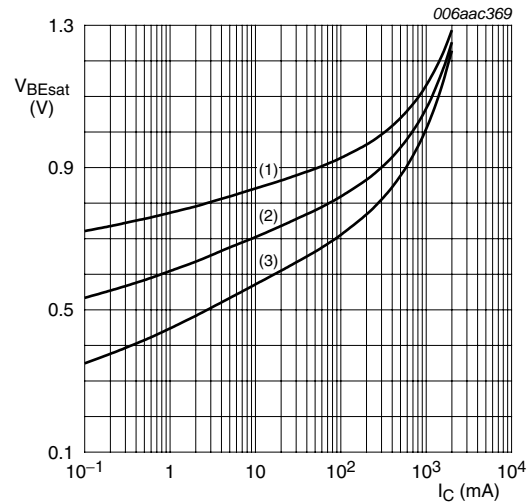
$T_{amb} = 25^\circ C$

**Fig 4. Collector current as a function of collector-emitter voltage; typical values**



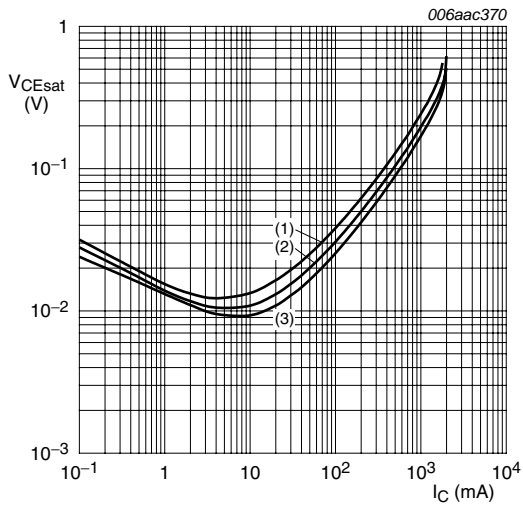
$V_{CE} = 10\text{ V}$   
 (1)  $T_{amb} = -55^\circ C$   
 (2)  $T_{amb} = 25^\circ C$   
 (3)  $T_{amb} = 100^\circ C$

**Fig 5. Base-emitter voltage as a function of collector current; typical values**



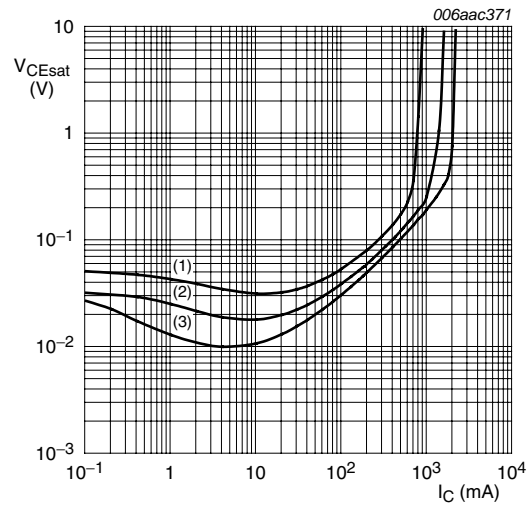
$I_C/I_B = 5$   
 (1)  $T_{amb} = -55^\circ C$   
 (2)  $T_{amb} = 25^\circ C$   
 (3)  $T_{amb} = 100^\circ C$

**Fig 6. Base-emitter saturation voltage as a function of collector current; typical values**



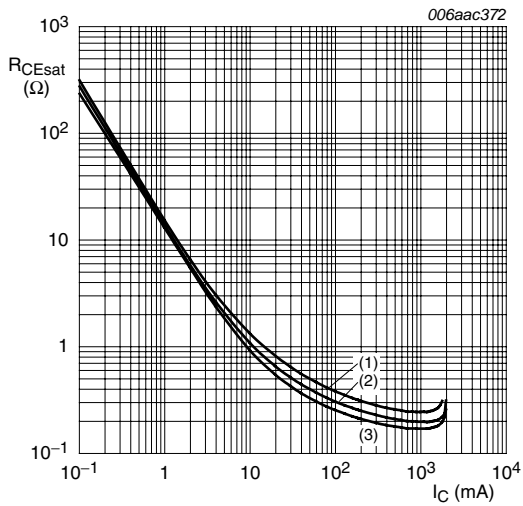
- $I_C/I_B = 5$
- (1)  $T_{amb} = 100\text{ °C}$
  - (2)  $T_{amb} = 25\text{ °C}$
  - (3)  $T_{amb} = -55\text{ °C}$

**Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values**



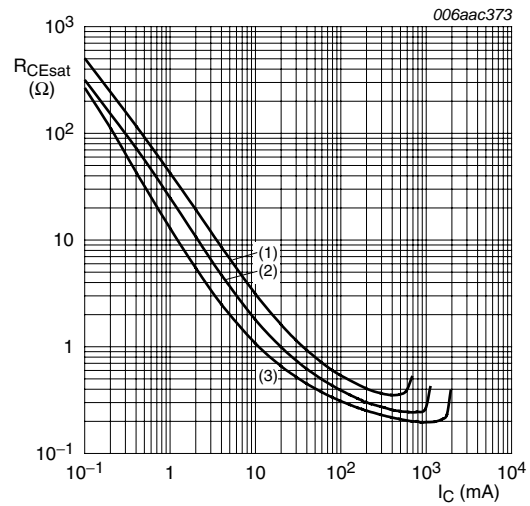
- $T_{amb} = 25\text{ °C}$
- (1)  $I_C/I_B = 20$
  - (2)  $I_C/I_B = 10$
  - (3)  $I_C/I_B = 5$

**Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values**



- $I_C/I_B = 5$
- (1)  $T_{amb} = 100\text{ °C}$
  - (2)  $T_{amb} = 25\text{ °C}$
  - (3)  $T_{amb} = -55\text{ °C}$

**Fig 9. Collector-emitter saturation resistance as a function of collector current; typical values**

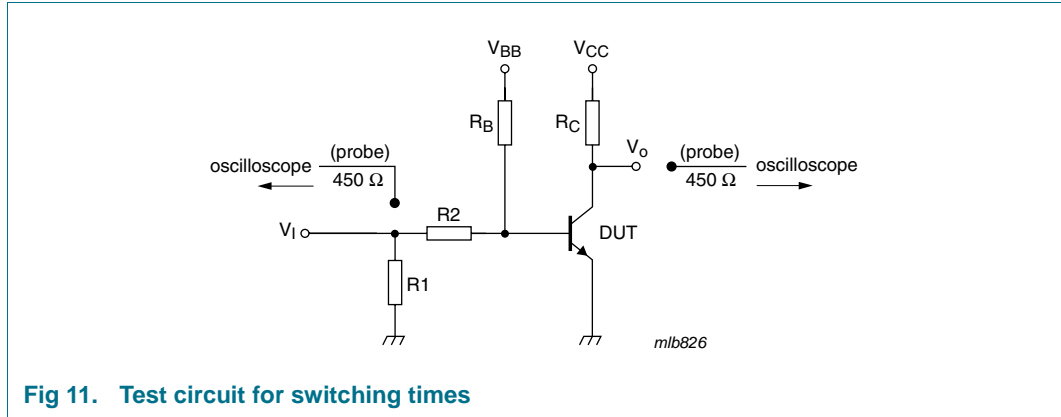


- $T_{amb} = 25\text{ °C}$
- (1)  $I_C/I_B = 20$
  - (2)  $I_C/I_B = 10$
  - (3)  $I_C/I_B = 5$

**Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values**



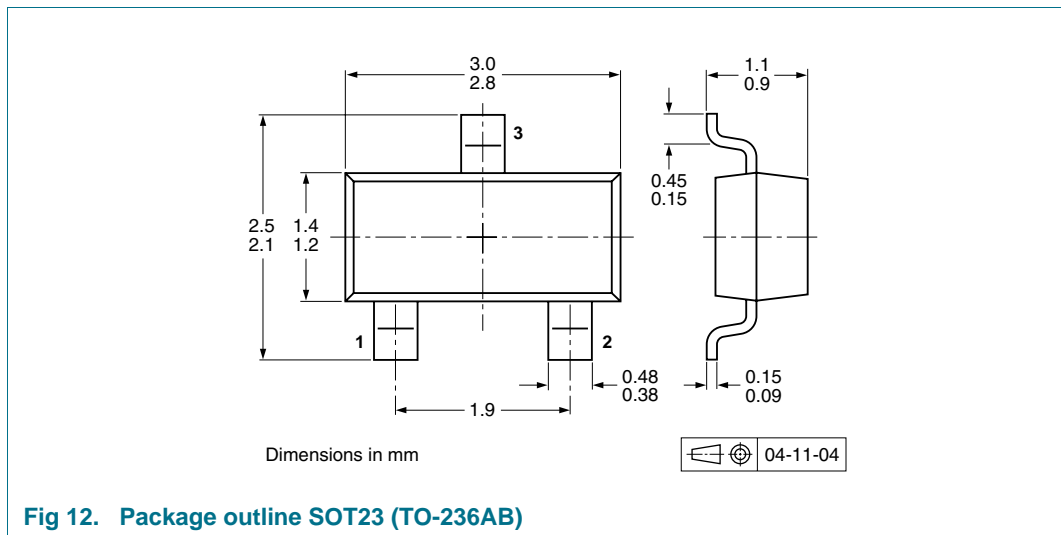
## 8. Test information



### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline



## 10. Packing information

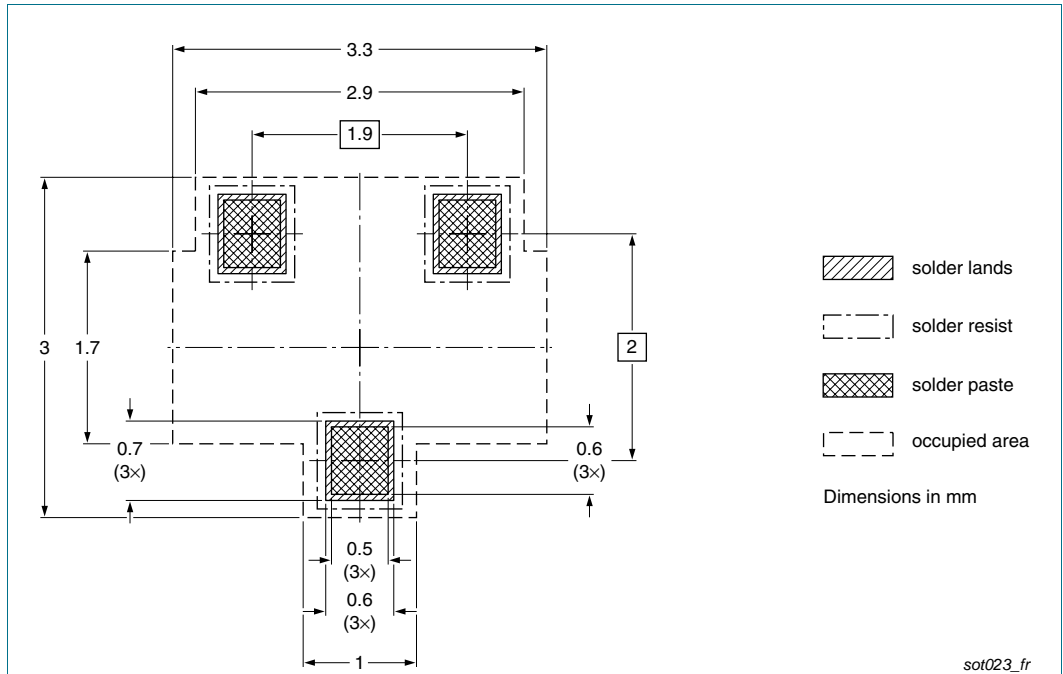
**Table 8. Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

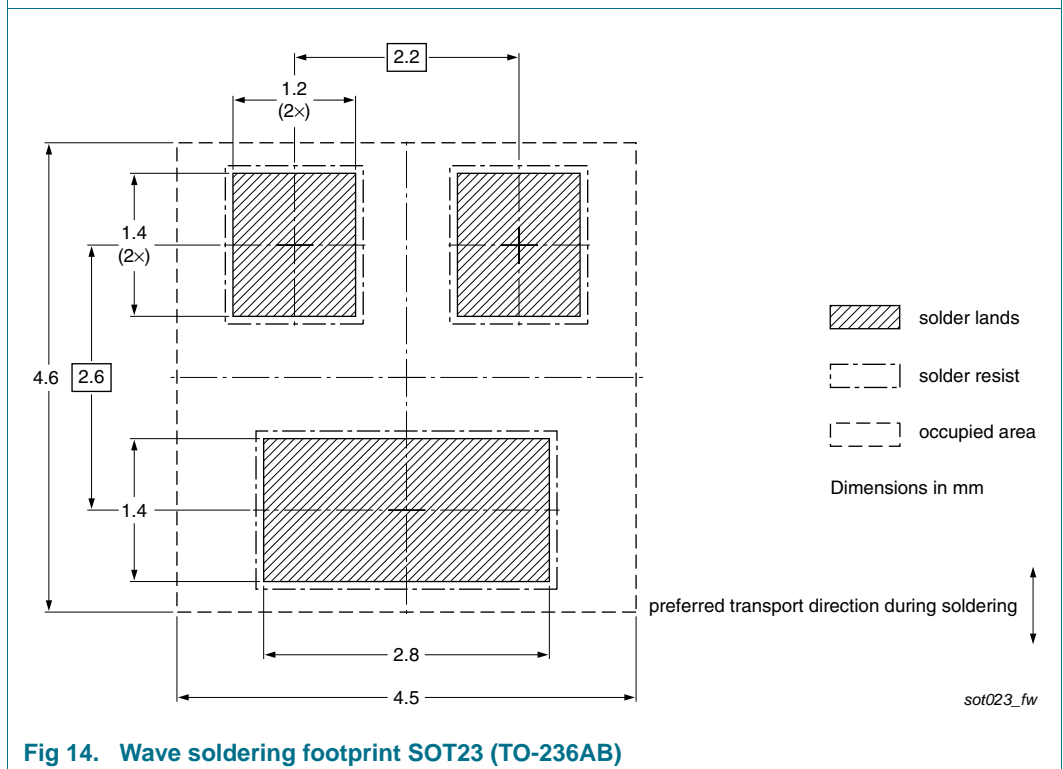
| Type number | Package | Description                    | Packing quantity |       |
|-------------|---------|--------------------------------|------------------|-------|
|             |         |                                | 3000             | 10000 |
| PBHV8118T   | SOT23   | 4 mm pitch, 8 mm tape and reel | -215             | -235  |

[1] For further information and the availability of packing methods, see [Section 14](#).

## 11. Soldering



**Fig 13. Reflow soldering footprint SOT23 (TO-236AB)**



**Fig 14. Wave soldering footprint SOT23 (TO-236AB)**

## 12. Revision history

Table 9. Revision history

| Document ID   | Release date | Data sheet status  | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PBHV8118T v.1 | 20100507     | Product data sheet | -             | -          |

## 13. Legal information

### 13.1 Data sheet status

| Document status <sup>[1][2]</sup> | Product status <sup>[3]</sup> | Definition  |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet      | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet    | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet        | Production                    | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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 Document identifier: PBHV8118T

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